

forming at least one semiconductor layer on said porous layer; and

separating said semiconductor layer from said substrate by forming a mechanical rupture in said porous layer.

<sup>97</sup>  
98. A method for separating a semiconductor layer from a substrate according to claim ~~1~~<sub>97</sub> wherein said substrate is a Si substrate.

<sup>97</sup>  
99. A method for separating a semiconductor layer from a substrate according to claim ~~1~~<sub>97</sub> wherein said porous layer is a Si porous layer.

<sup>97</sup>  
100. A method for separating a semiconductor layer from a substrate according to claim ~~1~~<sub>97</sub> wherein the method further comprises a step of oxidizing said porous layer after forming said porous layer.

<sup>100</sup>  
101. A method for separating a semiconductor layer from a substrate according to claim ~~4~~<sub>100</sub> wherein said porous layer is oxidized at a temperature of 400°.

102. A method for separating a semiconductor layer from a substrate comprising:

forming a porous layer on a surface of a substrate;

oxidizing said porous layer;